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**Inventor Name Search Result**

Your Search was:

Last Name = UDAGAWA

First Name = TAKASHI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>06228350</u>	4348981	150	01/26/1981	VERTICAL TYPE VAPOR-PHASE GROWTH APPARATUS	UDAGAWA, TAKASHI
<u>06675443</u>	Not Issued	161	11/27/1984	SEMICONDUCTOR VAPOR-PHASE GROWTH APPARATUS AND METHOD	UDAGAWA, TAKASHI
<u>06796438</u>	4755435	150	11/08/1985	PROCESS FOR COATING STEEL PANELS	UDAGAWA, TAKASHI
<u>06796450</u>	4756975	150	11/08/1985	PROCESS FOR COATING AUTOMOTIVE OUTER BODIES	UDAGAWA, TAKASHI
<u>06805382</u>	4755434	150	12/04/1985	PROCESS FOR COATING METALLIC SUBSTRATE	UDAGAWA, TAKASHI
<u>06806795</u> AB	Not Issued	161	12/09/1985	PROCESS FOR COATING METALLIC SUBSTRATE	UDAGAWA, TAKASHI
<u>06907212</u> AB	Not Issued	166	09/12/1986	PROCESS FOR COATING METALLIC SUBSTRATE	UDAGAWA, TAKASHI
<u>07050480</u> AB	Not Issued	166	05/18/1987	PROCESS FOR COATING METALLIC SUBSTRATE	UDAGAWA, TAKASHI
<u>07296342</u>	4983454	250	01/09/1989	PROCESS FOR COATING METALLIC SUBSTRATE	UDAGAWA, TAKASHI
<u>07296343</u>	5011733	150	01/09/1989	PROCESS FOR COATING METALLIC SUBSTRATE	UDAGAWA, TAKASHI
<u>08906935</u>	5886367	150	08/06/1997	EPITAXIAL WAFER DEVICE INCLUDING AN ACTIVE LAYER HAVING A TWO-PHASE STRUCTURE AND LIGHT-EMITTING DEVICE USING THE WAFER	UDAGAWA, TAKASHI
<u>09073765</u>	6268618	150	05/07/1998	ELECTRODE FOR LIGHT-EMITTING SEMICONDUCTOR DEVICES AND METHOD OF PRODUCING THE ELECTRODE	UDAGAWA, TAKASHI
<u>09170265</u>	6110757	150	10/13/1998	METHOD OF FORMING EPITAXIAL WAFER FOR LIGHT-	UDAGAWA, TAKASHI

				EMITTING DEVICE INCLUDING AN ACTIVE LAYER HAVING A TWO-PHASE STRUCTURE	
<u>09204280</u>	<u>6541797</u>	150	12/03/1998	GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE	UDAGAWA, TAKASHI
<u>09217629</u>	<u>6147363</u>	150	12/22/1998	NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND MANUFACTURING METHOD OF THE SAME	UDAGAWA, TAKASHI
<u>09270749</u>	<u>6069021</u>	150	03/17/1999	METHOD OF GROWING GROUP III NITRIDE SEMICONDUCTOR CRYSTAL LAYER AND SEMICONDUCTOR DEVICE INCORPORATING GROUP III NITRIDE SEMICONDUCTOR CRYSTAL LAYER	UDAGAWA, TAKASHI
<u>09438788</u>	<u>6153894</u>	150	11/12/1999	GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE	UDAGAWA, TAKASHI
<u>09500450</u>	<u>6194744</u>	150	02/09/2000	Method of growing group III nitride semiconductor crystal layer and semiconductor device incorporating group III nitride semiconductor crystal layer	UDAGAWA, TAKASHI
<u>09599725</u>	<u>6346719</u>	150	06/23/2000	AlgalnP light-emitting diode	UDAGAWA, TAKASHI
<u>09624221</u>	<u>6335219</u>	150	07/24/2000	Nitride semiconductor light-emitting device and manufacturing method of the same	UDAGAWA, TAKASHI
<u>09656822</u> No D <sub>2</sub>	Not Issued	161	09/07/2000	Group III nitride semiconductor light-emitting device and process for producing the device	UDAGAWA, TAKASHI
<u>09662587</u>	<u>6462361</u>	150	09/15/2000	GAINP EPITAXIAL STACKING STRUCTURE AND FABRICATION METHOD THEREOF, AND A FET TRANSISTOR USING THIS STRUCTURE	UDAGAWA, TAKASHI
<u>09691057</u>	<u>6512248</u>	150	10/19/2000	SEMICONDUCTOR LIGHT-EMITTING DEVICE, ELECTRODE FOR THE DEVICE, METHOD FOR FABRICATING THE ELECTRODE, LED LAMP USING THE DEVICE, AND LIGHT SOURCE USING THE LED LAMP	UDAGAWA, TAKASHI
<u>09694319</u>	<u>6326223</u>	150	10/24/2000	Electrode for light-emitting	UDAGAWA, TAKASHI

				semiconductor devices and method of producing the electrode	
<u>09694325</u>	<u>6403987</u>	150	10/24/2000	ELECTRODE FOR LIGHT-EMITTING SEMICONDUCTOR DEVICES	UDAGAWA, TAKASHI
<u>09838338</u>	<u>6531716</u>	150	04/20/2001	GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND MANUFACTURING METHOD FOR THE SAME	UDAGAWA, TAKASHI
<u>09842045</u>	<u>6645302</u>	150	04/26/2001	VAPOR PHASE DEPOSITION SYSTEM	UDAGAWA, TAKASHI
<u>09881782</u>	<u>6984851</u>	150	06/18/2001	GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, LIGHT-EMITTING DIODE LAMP, LIGHT SOURCE, ELECTRODE FOR GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE, AND METHOD FOR PRODUCING THE ELECTRODE	UDAGAWA, TAKASHI
<u>09885943</u>	<u>6787814</u>	150	06/22/2001	GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DEVICE AND PRODUCTION METHOD THEREOF	UDAGAWA, TAKASHI
<u>10001815</u>	<u>6664575</u>	150	12/05/2001	GAINP STACKED LAYER STRUCTURE AND FIELD-EFFECT TRANSISTOR MANUFACTURED USING THE SAME	UDAGAWA, TAKASHI
<u>10076425</u>	<u>6541799</u>	150	02/19/2002	GROUP-III NITRIDE SEMICONDUCTOR LIGHT-EMITTING DIODE	UDAGAWA, TAKASHI
<u>10136377</u>	<u>6800501</u>	150	05/02/2002	ELECTRODE FOR LIGHT-EMITTING SEMICONDUCTOR DEVICES AND METHOD OF PRODUCING THE ELECTRODE	UDAGAWA, TAKASHI
<u>10180059</u>	<u>6797990</u>	150	06/27/2002	BORON PHOSPHIDE-BASED SEMICONDUCTOR DEVICE AND PRODUCTION METHOD THEREOF	UDAGAWA, TAKASHI
<u>10190835</u>	<u>6841435</u>	150	07/09/2002	METHOD FOR FABRICATING A GAINP EPITAXIAL STACKING STRUCTURE	UDAGAWA, TAKASHI
<u>10207901</u>	<u>6835962</u>	150	07/31/2002	STACKED LAYER STRUCTURE,	UDAGAWA, TAKASHI

				LIGHT-EMITTING DEVICE, LAMP, AND LIGHT SOURCE UNIT	
<u>10237732</u>	<u>6730987</u>	150	09/10/2002	COMPOUND SEMICONDUCTOR DEVICE, PRODUCTION METHOD THEREOF, LIGHT-EMITTING DEVICE AND TRANSISTOR	UDAGAWA, TAKASHI
<u>10265148</u>	<u>6677615</u>	150	10/07/2002	SEMICONDUCTOR LIGHT- EMITTING DEVICE, ELECTRODE FOR THE DEVICE, METHOD FOR FABRICATING THE ELECTRODE, LED LAMP USING THE DEVICE, AND LIGHT SOURCE USING THE LED LAMP	UDAGAWA, TAKASHI
<u>10332200</u>	Not Issued	71	01/07/2003	Semiconductor device, semiconductor layer and production method thereof	UDAGAWA, TAKASHI
<u>10353006</u>	<u>6730941</u>	150	01/29/2003	BORON PHOSPHIDE-BASED SEMICONDUCTOR LIGHT- EMITTING DEVICE, PRODUCTION METHOD THEREOF, AND LIGHT- EMITTING DIODE	UDAGAWA, TAKASHI
<u>10363315</u>	<u>6876013</u>	150	03/03/2003	COMPOUND SEMICONDUCTOR MULTILAYER STRUCTURE AND BIPOLAR TRANSISTOR USING THE SAME	UDAGAWA, TAKASHI
<u>10369556</u>	<u>6846754</u>	150	02/21/2003	BORON PHOSPHIDE-BASED SEMICONDUCTOR LAYER AND VAPOR PHASE GROWTH METHOD THEREOF	UDAGAWA, TAKASHI
<u>10370761</u>	<u>6831304</u>	150	02/24/2003	P-N JUNCTION TYPE BORON PHOSPHIDE-BASED SEMICONDUCTOR LIGHT- EMITTING DEVICE AND PRODUCTION METHOD THEREOF	UDAGAWA, TAKASHI
<u>10384666</u>	<u>6774402</u>	150	03/11/2003	PN-JUNCTION TYPE COMPOUND SEMICONDUCTOR LIGHT- EMITTING DEVICE, PRODUCTION METHOD THEREOF AND WHITE LIGHT- EMITTING DIODE	UDAGAWA, TAKASHI
<u>10389904</u>	<u>6831293</u>	150	03/18/2003	P-N JUNCTION-TYPE COMPOUND SEMICONDUCTOR LIGHT-EMITTING DEVICE, PRODUCTION METHOD THEREOF, LAMP AND LIGHT	UDAGAWA, TAKASHI

				SOURCE	
<u>10467677</u>	<u>7018728</u>	150	08/11/2003	BORON PHOSPHIDE-BASED SEMICONDUCTOR DEVICE AND PRODUCTION METHOD THEREOF	UDAGAWA, TAKASHI
<u>10486985</u> <i>no DP</i>	Not Issued	83	02/18/2004	Multicolor light-emitting lamp and light source	UDAGAWA, TAKASHI
<u>10502597</u> <i>no DP</i>	Not Issued	30	01/14/2005	Boron phosphide-based semiconductor device production method thereof light-emitting diode and boron phosphide-based semiconductor layer	UDAGAWA, TAKASHI
<u>10517069</u> <i>no DP</i>	Not Issued	41 <i>(not rel.)</i>	12/03/2004	Reciprocating pump type spout unit	UDAGAWA, TAKASHI
<u>10535821</u> <i>no DP</i>	Not Issued	71	05/23/2005	Boron phosphide-based compound semiconductor device, production method thereof and light-emitting diode	UDAGAWA, TAKASHI
<u>10536410</u> <i>no DP</i>	Not Issued	41	05/26/2005	Boron phosphide-based compound semiconductor device, production method thereof and light-emitting diode	UDAGAWA, TAKASHI

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